

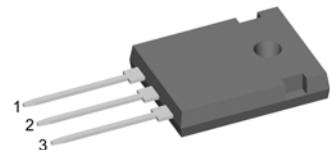
XPT IGBT

V_{CES} = 1200V
 I_{C25} = 38A
 $V_{CE(sat)}$ = 1.8V

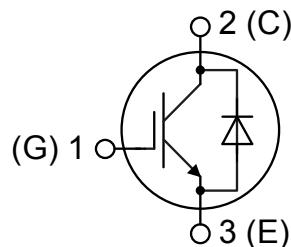
Copack

Part number

IXA20IF1200HB



Backside: collector



Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_c
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

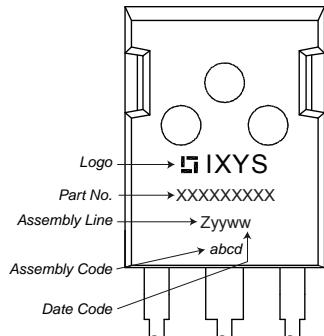
Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

IGBT			Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^\circ C$			1200	V	
V_{GES}	max. DC gate voltage				± 20	V	
V_{GEM}	max. transient gate emitter voltage				± 30	V	
I_{C25}	collector current	$T_c = 25^\circ C$			38	A	
I_{C80}		$T_c = 80^\circ C$			22	A	
P_{tot}	total power dissipation	$T_c = 25^\circ C$			165	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_c = 15 A; V_{GE} = 15 V$	$T_{VJ} = 25^\circ C$		1.8	V	
			$T_{VJ} = 125^\circ C$		2.1	V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_c = 0.6 mA; V_{GE} = V_{CE}$	$T_{VJ} = 25^\circ C$	5.4	5.9	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0 V$	$T_{VJ} = 25^\circ C$		0.1	mA	
			$T_{VJ} = 125^\circ C$		0.1	mA	
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20 V$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600 V; V_{GE} = 15 V; I_c = 15 A$			47	nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600 V; I_c = 15 A$ $V_{GE} = \pm 15 V; R_G = 56 \Omega$			70	ns	
t_r	current rise time				40	ns	
$t_{d(off)}$	turn-off delay time				250	ns	
t_f	current fall time				100	ns	
E_{on}	turn-on energy per pulse				1.55	mJ	
E_{off}	turn-off energy per pulse				1.7	mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15 V; R_G = 56 \Omega$	$T_{VJ} = 125^\circ C$				
I_{CM}		$V_{CEmax} = 1200 V$			45	A	
SCSOA	short circuit safe operating area	$V_{CEmax} = 900 V$					
t_{sc}	short circuit duration	$V_{CE} = 900 V; V_{GE} = \pm 15 V$	$T_{VJ} = 125^\circ C$		10	μs	
I_{sc}	short circuit current	$R_G = 56 \Omega$; non-repetitive			60	A	
R_{thJC}	thermal resistance junction to case				0.76	K/W	
R_{thCH}	thermal resistance case to heatsink				0.25	K/W	
Diode							
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^\circ C$			1200	V	
I_{F25}	forward current	$T_c = 25^\circ C$			45	A	
I_{F80}		$T_c = 80^\circ C$			24	A	
V_F	forward voltage	$I_F = 20 A$	$T_{VJ} = 25^\circ C$		2.20	V	
			$T_{VJ} = 125^\circ C$		1.95	V	
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ C$		*	mA	
	* not applicable, see I_{CES} value above		$T_{VJ} = 125^\circ C$		*	mA	
Q_{rr}	reverse recovery charge	$V_R = 600 V$ $-di_F/dt = -400 A/\mu s$ $I_F = 20 A; V_{GE} = 0 V$			3	μC	
I_{RM}	max. reverse recovery current				20	A	
t_{rr}	reverse recovery time				350	ns	
E_{rec}	reverse recovery energy				0.7	mJ	
R_{thJC}	thermal resistance junction to case				0.9	K/W	
R_{thCH}	thermal resistance case to heatsink				0.25	K/W	

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

Product Marking



Part number

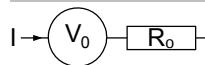
I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 20 = Current Rating [A]
 IF = Copack
 1200 = Reverse Voltage [V]
 HB = TO-247AD (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA20IF1200HB	IXA20IF1200HB	Tube	30	508460

Similar Part	Package	Voltage class
IXA20I1200PB	TO-220AB (3)	1200

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150$ °C

IGBT

Diode

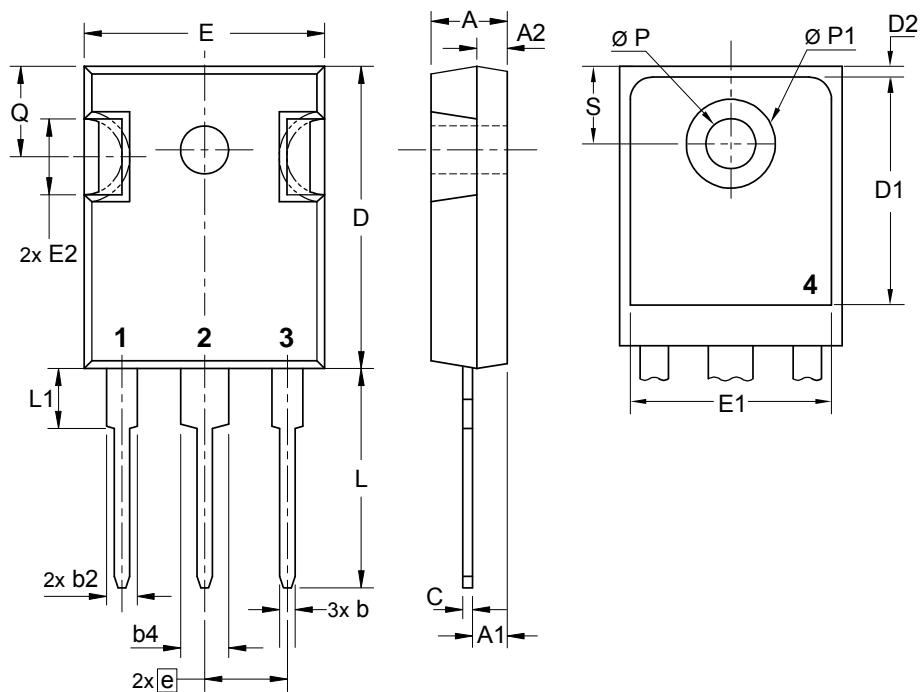
 $V_{0\max}$ threshold voltage

1.1 1.25 V

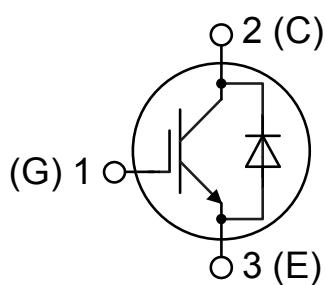
 $R_{0\max}$ slope resistance *

86 42.5 mΩ

Outlines TO-247



Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



IGBT

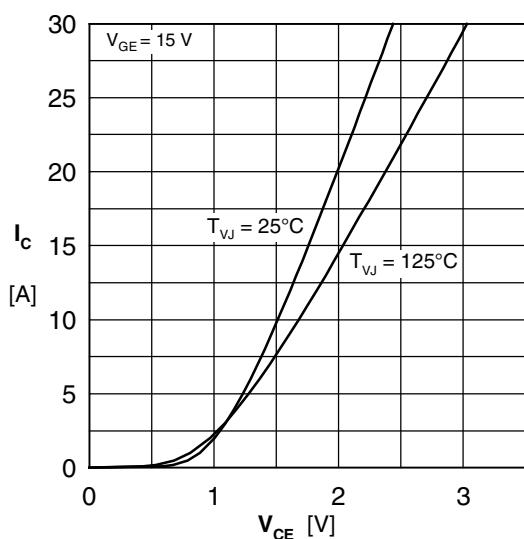


Fig. 1 Typ. output characteristics

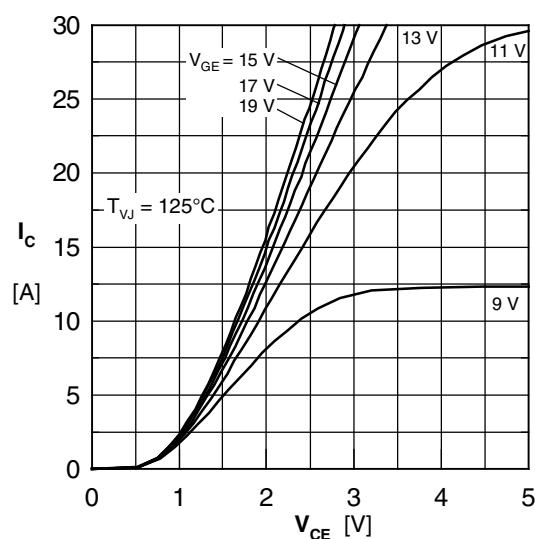


Fig. 2 Typ. output characteristics

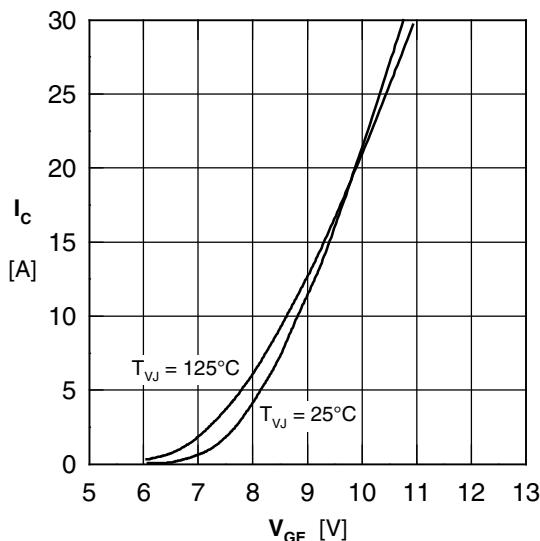


Fig. 3 Typ. tranfer characteristics

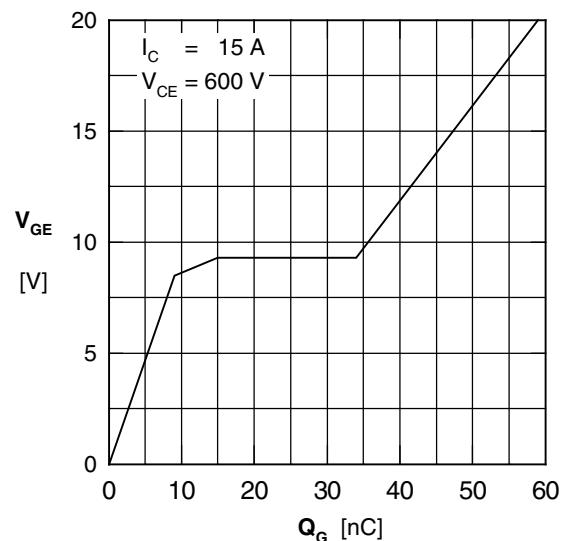


Fig. 4 Typ. turn-on gate charge

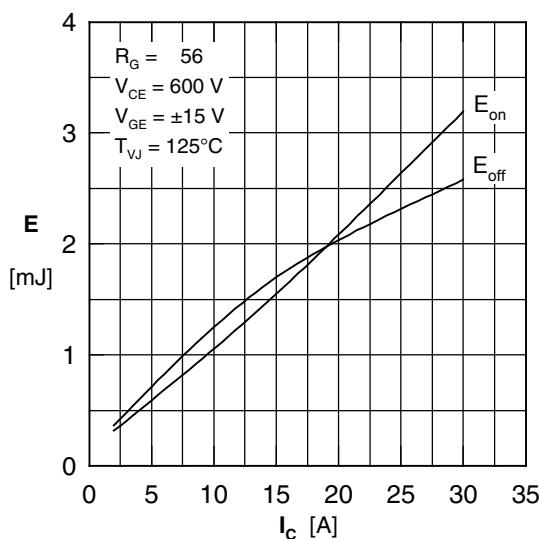


Fig. 5 Typ. switching energy vs. collector current

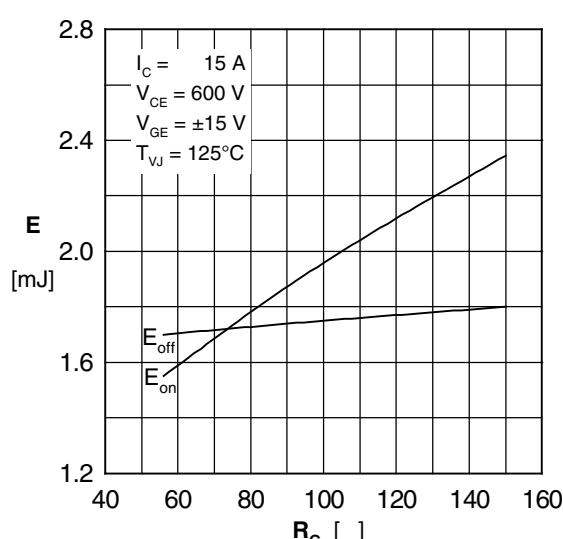


Fig. 6 Typ. switching energy vs. gate resistance

Diode

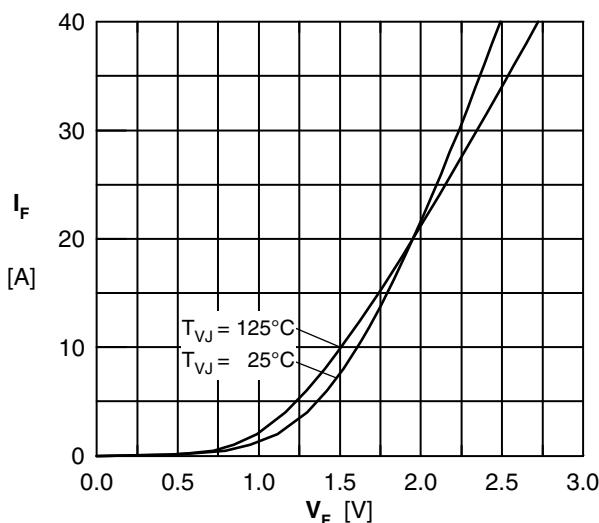
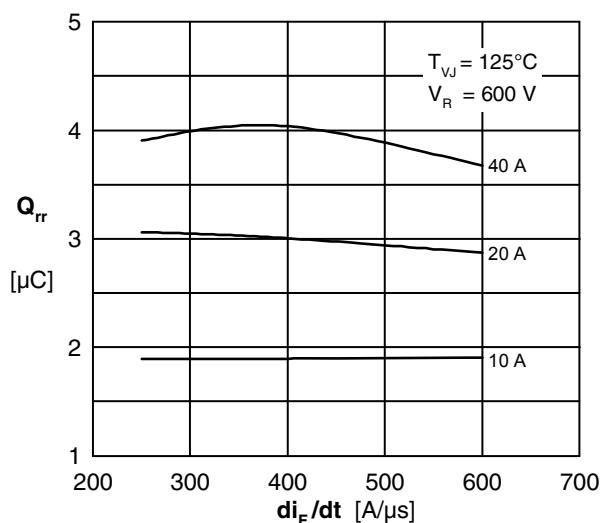
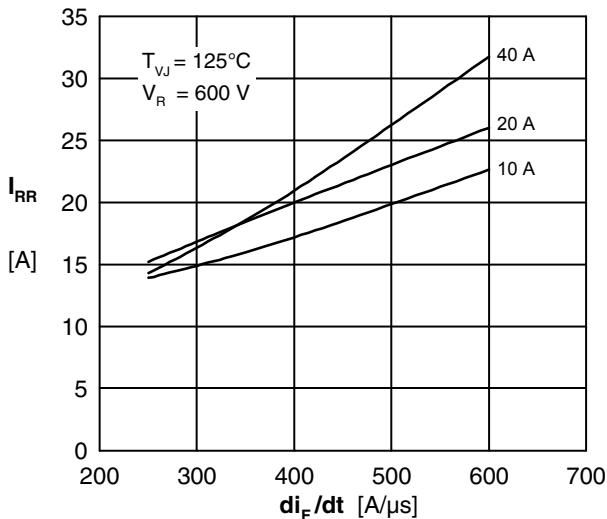
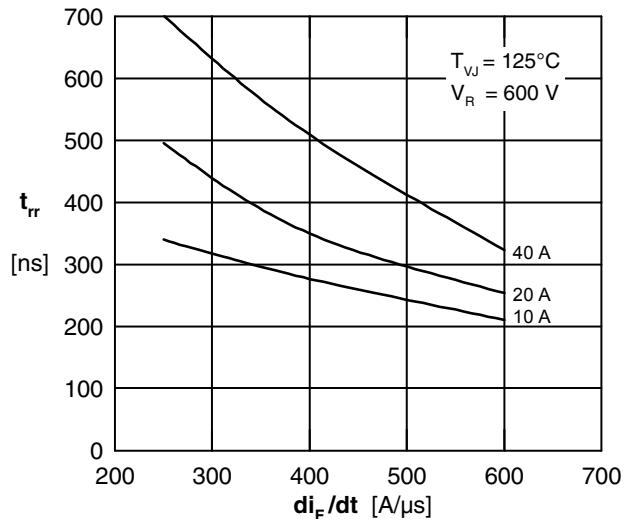
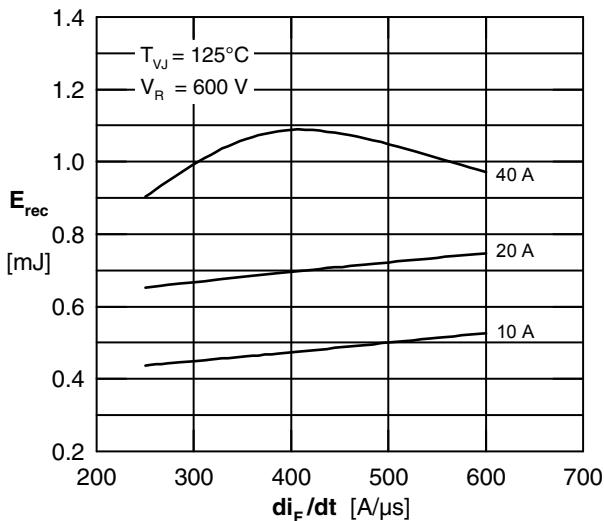
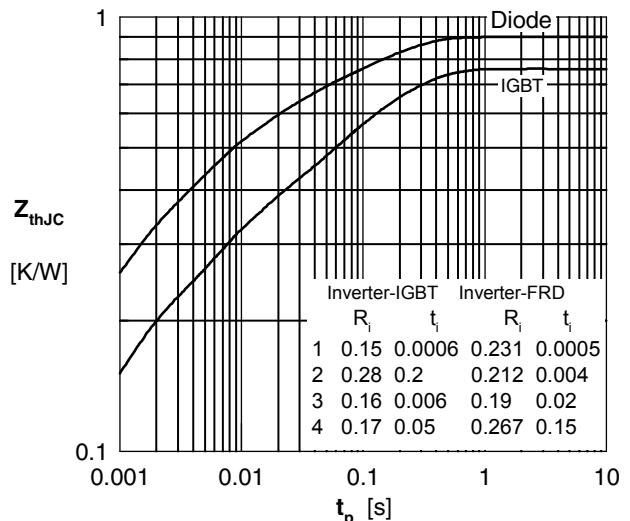
Fig. 7 Typ. Forward current versus V_F Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt Fig. 9 Typ. peak reverse current I_{rr} vs. di/dt Fig. 10 Typ. recovery time t_{rr} versus di/dt Fig. 11 Typ. recovery energy E_{rec} versus di/dt 

Fig. 12 Typ. transient thermal impedance



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